

Description

The HXY4435S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features SOP-8

 $V_{DS} = -30V I_{D} = -9A$

 $R_{DS(ON)}$ < 20m Ω @ V_{GS} =10V

Application

Battery protection

Load switch P-Channel MOSFET

Uninterruptible power supply

G S

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY4435S	SOP-8	4435 XXX YYYY	3000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
VGS	Gate-Source Voltage	<u>+</u> 20	V
I _D @T _A =25°C	Drain Current ³ , V _{GS} @ 10V	-9	Α
I _D @T _A =70°C	Drain Current ³ , V _{GS} @ 10V	-7.3	А
IDM	Pulsed Drain Current ¹	-50	А
P _D @T _A =25°C	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	50	°C/W



Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30	-	-	V
		V _{GS} =-10V, I _D =-7A	-	18	20	mΩ
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-5A	-	32	36	mΩ
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-	-3	V
g fs	Forward Transconductance	V _{DS} =-10V, I _D =-7A	-	16	-	S
IDSS	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	-	-	-30	uA
IGSS	Gate-Source Leakage	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Qg	Total Gate Charge	I _D =-7A	-	18	29	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-24V	-	3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	10	-	nC
td(on)	Turn-on Delay Time	V _{DS} =-15V	-	8	-	ns
t _r	Rise Time	I _D =-1A	-	6.6	-	ns
td(off)	Turn-off Delay Time	R _G =3.3Ω	-	44	-	ns
t _f	Fall Time	V _{GS} =-10V	-	34	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1175	1690	pF
Coss	Output Capacitance	V _{DS} =- 25V	-	195	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	190	-	pF
V_{SD}	Forward On Voltage ²	I _S =-2.1A, V _{GS} =0V	-	-	-1.2	V
trr	Reverse Recovery Time	I _S =-7A, V _{GS} =0V, dI/dt=100A/µs	-	28	-	ns
Qrr	Reverse Recovery Charge		-	18	-	nC

Notes:

- 1. Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤10sec; 125 °C/W when mounted on Min. cop

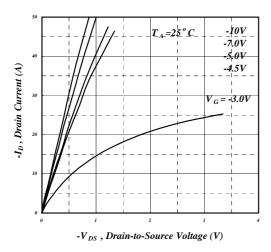


Fig 1. Typical Output Characteristics

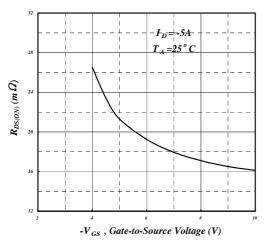


Fig 3. On-Resistance v.s. Gate Voltage

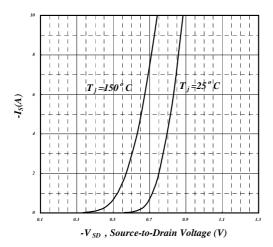


Fig 5. Forward Characteristic of Reverse Diode

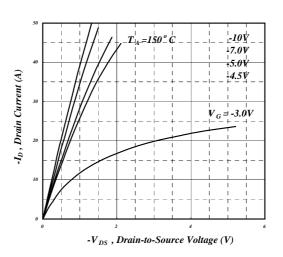


Fig 2. Typical Output Characteristics

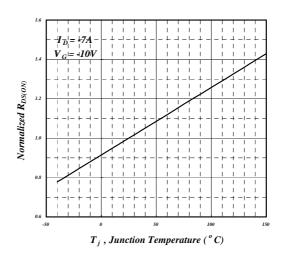


Fig 4. Normalized On-Resistance v.s. Junction Temperature

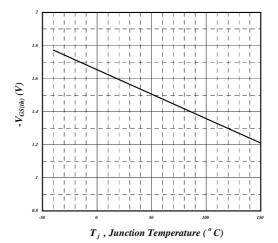


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

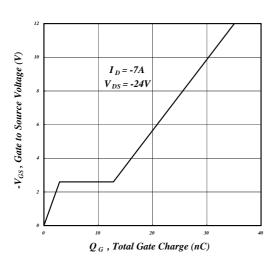


Fig 7. Gate Charge Characteristics

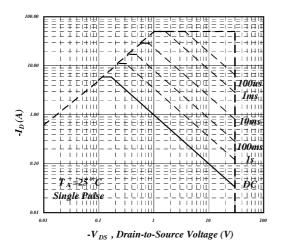


Fig 9. Maximum Safe Operating Area

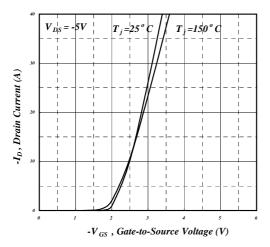


Fig 11. Transfer Characteristics

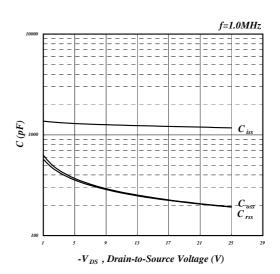


Fig 8. Typical Capacitance Characteristics

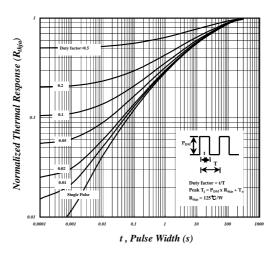


Fig 10. Effective Transient Thermal Impedance

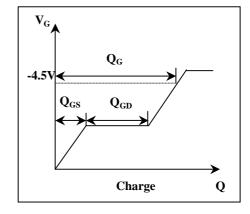
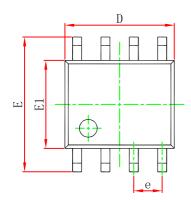
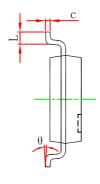


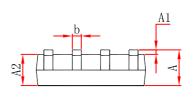
Fig 12. Gate Charge Circuit



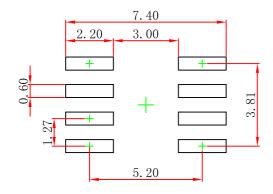
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min	Max	Min	Max		
A	1. 350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
c	0.170	0.250	0.007	0.010		
D	4.800	5.000	0.189	0.197		
e	1. 270 (1.270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0. 228	0. 244		
E1	3.800	4.000	0.150	0. 157		
L	0.400	1. 270	0.016	0.050		
θ	0°	8°	0°	8°		



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

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